

## Features

- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

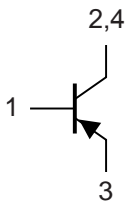
## Maximum Ratings @ 25°C Unless Otherwise Specified

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 250°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-1.5	A
Collector Power Dissipation	$P_C$	500	mW

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

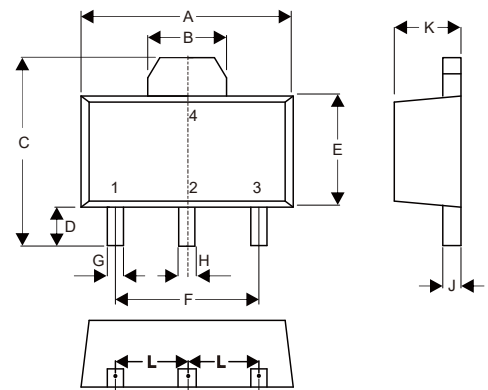
## Internal Structure



1.BASE  
2,4.COLLECTOR  
3.EMITTER

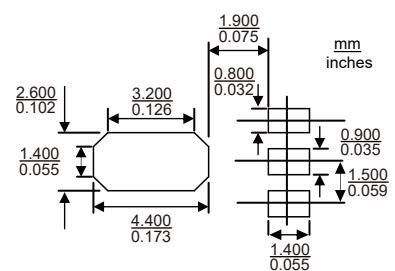
# PNP Silicon Plastic Encapsulate Transistors

## SOT-89



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.169	0.185	4.30	4.70	
B	0.061		1.55		TYP.
C	0.154	0.171	3.91	4.35	
D	0.031	0.047	0.80	1.20	
E	0.089	0.104	2.25	2.65	
F	0.118		3.00		TYP.
G	0.013	0.020	0.33	0.52	
H	0.015	0.021	0.38	0.53	
J	0.014	0.017	0.35	0.44	
K	0.055	0.063	1.40	1.60	
L	0.059		1.50		TYP.

## Suggested Solder Pad Layout



**Electrical Characteristics @ 25°C Unless Otherwise Specified**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40			V	$I_C=-100\mu A, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25			V	$I_C=-0.1mA, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu A, I_C=0$
Collector-Base Cutoff Current	$I_{CBO}$			-0.1	$\mu A$	$V_{CB}=-40V, I_E=0$
Collector-Emitter Cutoff Current	$I_{CEO}$			-0.1	$\mu A$	$V_{CE}=-20V, I_C=0$
Emitter-Base Cutoff Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB}=-5.0V, I_C=0$
DC Current Gain	$h_{FE(1)}$	85		400		$V_{CE}=-1.0V, I_C=-100mA$
	$h_{FE(2)}$	40				$V_{CE}=-1.0V, I_C=-800mA$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C=-800mA, I_B=-80mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.2	V	$I_C=-800mA, I_B=-80mA$
Base-Emitter Positive Favor Voltage	$V_{BEF}$			-1.55	V	$I_B=-1.0A$
Transition Frequency	$f_T$	100			MHz	$V_{CE}=-10V, I_C=-50mA, f=30MHz$
Output Capacitance	$C_{ob}$			15	pF	$V_{CB}=-10V, I_E=0, f=1MHz$

**Classification Of  $h_{FE(1)}$** 

Rank	PXT8550-B	PXT8550-C	PXT8550-D	PXT8550-D3
Range	85-160	120-200	160-300	300-400
Marking	Y2	Y2	Y2	Y2

### Curve Characteristics

Fig. 1 - Static Characteristics

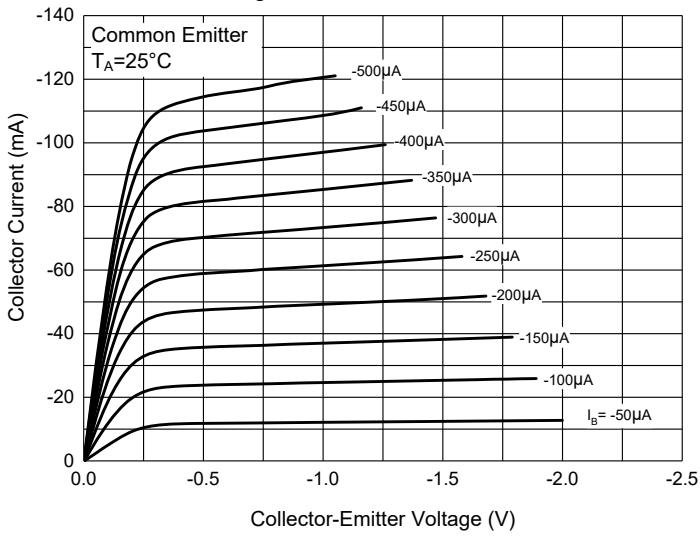


Fig. 2 - DC Current Gain Characteristics

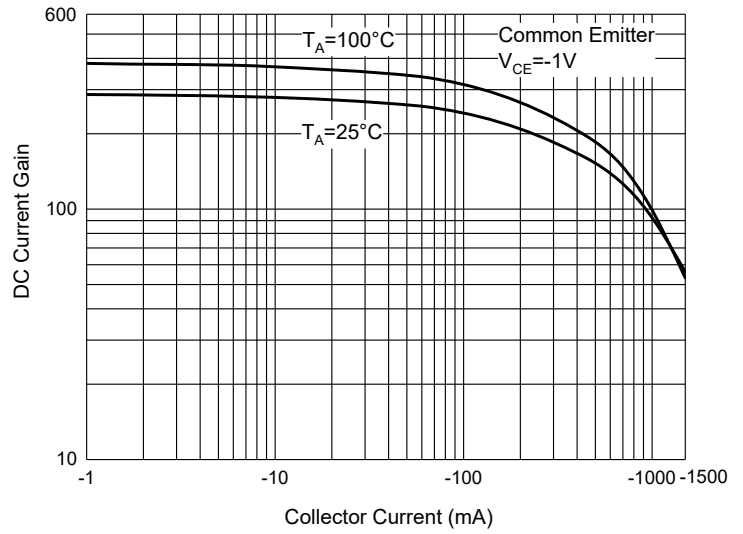


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

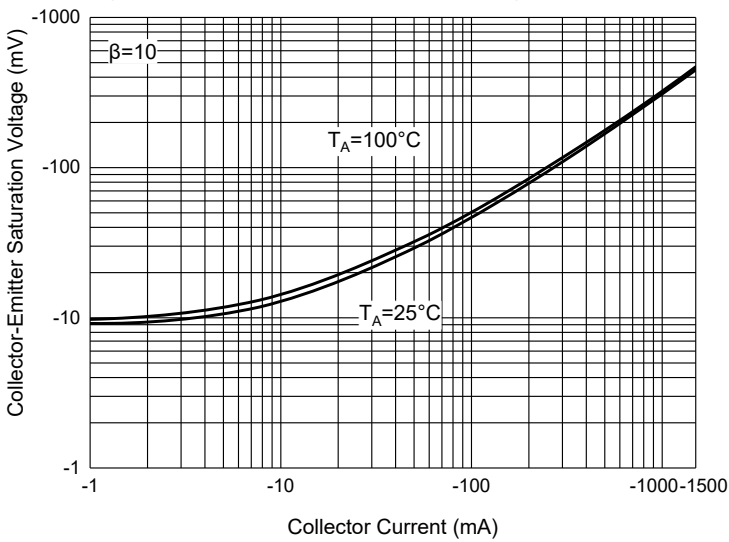


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

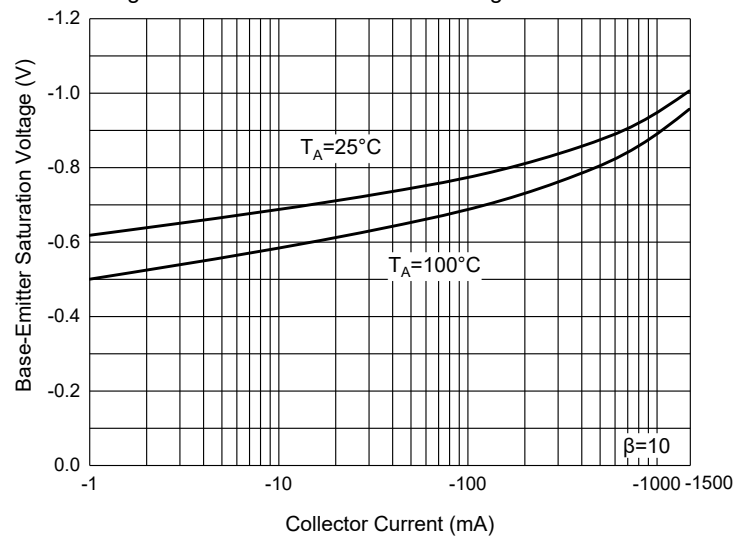


Fig. 5 - Base-Emitter Voltage Characteristics

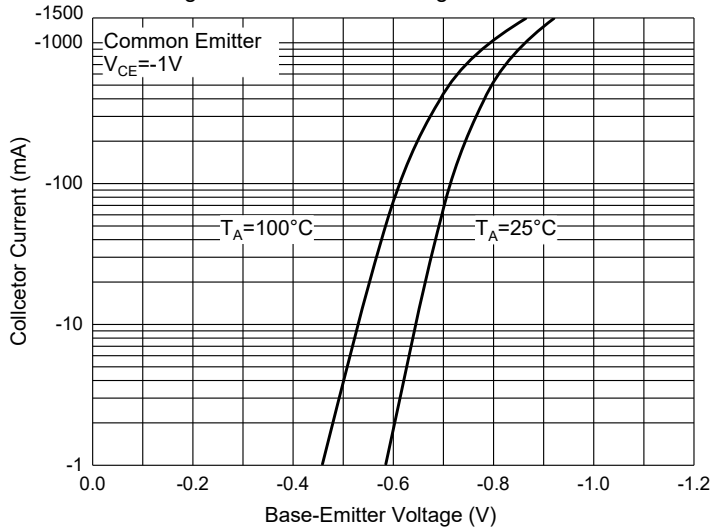


Fig. 6 - Power Derating Curve

